

**Amendments to the Claims:**

1. (Cancelled)

2. (Currently Amended) An image sensor as claimed in claim 1, comprising a semiconductor body having a first conductivity type and having a surface, the surface being provided with a number of cells, a cell comprising a photosensitive element and a reset transistor, the reset transistor comprising a source region, a drain region and a gate region, the source region and the drain region having a second conductivity type opposite to the first conductivity type, the source region of the reset transistor being electrically connected to the photosensitive element,

wherein a well region is present which well region extends from the surface into the semiconductor body and extends at least partly below the gate region and the well region having a first conductivity type, the source region extending at least substantially in a doped region of the photosensitive element, the doped region having a second conductivity type,

wherein the source region extends beyond the doped region of the photosensitive element, and

wherein the source region extends into the well region, and the gate region overlaps the source region such that a portion of the source region is sandwiched between the gate region and the well region.

3. (Currently Amended) An image sensor as claimed in claim 2, wherein the drain region extends in the well region.

4. (Cancelled)

5. (Currently Amended) An image sensor as claimed in claim 2, wherein the gate region is positioned along an edge of the photosensitive element.

6. (Currently Amended) ~~An image sensor as claimed in claim 5~~ An image sensor comprising a semiconductor body having a first conductivity type and having a surface, the surface being provided with a number of cells, a cell comprising a photosensitive element and a reset transistor, the reset transistor comprising a source region, a drain region and a gate region, the source region and the drain region having a second conductivity type opposite to the first conductivity type, the source region of the reset transistor being electrically connected to the photosensitive element,

wherein a well region is present which well region extends from the surface into the semiconductor body and extends at least partly below the gate region and the well region having the first conductivity type, the source region extending at least substantially in a doped region of the photosensitive element, the doped region having the second conductivity type,

wherein the source region extends beyond the doped region of the photosensitive element, and

wherein a source follower transistor is present having a gate connected to the source region of the reset transistor, the gate of the reset transistor having a length which is ~~longer~~ greater than ~~the~~ a length of the gate of the source follower transistor.

7. (Currently Amended) The image sensor as claimed in claim 2[41], wherein the source region extends beyond the doped region of the photosensitive element into the well region.

8. (Withdrawn) A method of manufacturing a CMOS image sensor comprising the steps of:

- forming a photosensitive element in a semiconductor substrate having a first conductivity type by providing dopant atoms into a region in the semiconductor substrate, the dopant atoms having a second conductivity type in the region opposite to the first conductivity type,
- using a protection mask over the region of the photosensitive element after which a well region is formed by implanting ions having a first conductivity type in the semiconductor substrate,

- forming a gate region by depositing a layer of gate material and patterning the layer, wherein the gate region is formed over a side-wall of the well region, the side-wall being present between the region of the photosensitive element and the well region.

9. (Withdrawn) A method as claimed in claim 8, wherein a source region is formed by implanting ions of a second conductivity type self-aligned to the gate, and the source region is at least substantially formed in the region of the photosensitive element.

10. (Withdrawn) A method as claimed in claim 8, wherein a distance is formed between the source region and the well region.

11. (Withdrawn) A method as claimed in claim 8, wherein field isolation is formed on the semiconductor substrate and the photosensitive element is formed by implantation of the ions of the second conductive type through the field isolation.

12. (Withdrawn) A method as claimed in claim 11, wherein the photosensitive element has an edge formed by the field isolation and the gate is positioned along that edge.

13. (Currently Amended) The image sensor of claim 12, wherein the gate region does not extend beyond the well region.

14. (Withdrawn - Currently Amended) The image sensor of claim 12, wherein the gate region extends beyond the well region, and wherein the gate region does not extend above the doped region of the photosensitive element.

15. (Withdrawn - Currently Amended) The image sensor of claim 12, wherein the source region does not extend into the well region.

16. (Cancelled)

17. (Cancelled)

18. (Withdrawn - Currently Amended) The image sensor of claim 42, wherein the source region extends beyond the doped region of the photosensitive element

19. (Cancelled)

20. (New) The image sensor as claimed in claim 2, wherein an edge of the gate region extending over the source region is disposed adjacent on an edge of the well region.

21. (New) The image sensor as claimed in claim 20, wherein the edge of the well region abuts an edge of the photosensitive element, such that the edge of the gate region is adjacent to the edge of the photosensitive element.

22. (New) The image sensor as claimed in claim 2, wherein a source follower transistor is present having a gate connected to the source region of the reset transistor, the gate of the reset transistor having a length which is greater than a length of the gate of the source follower transistor.